

2020 Research Day

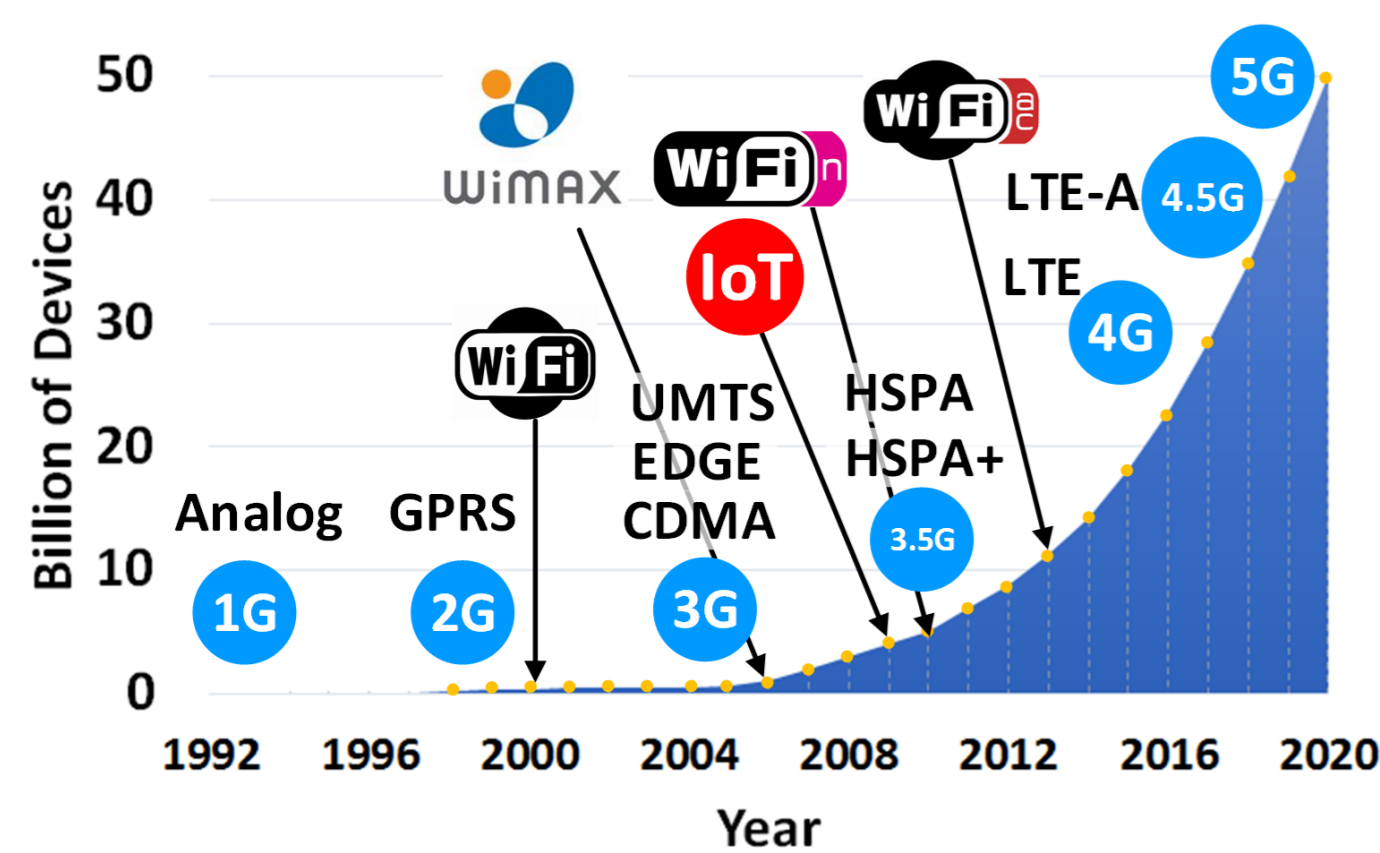
Reconfigurable Radiofrequency Circuits

based on Phase-Change Materials

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INTRODUCTION

EXPONENTIAL GROWTH OF MOBILE COMMUNICATIONS



- Exponential increase in number of wireless standards
- Large heterogeneity in mobile handsets
- Different chips for each standard

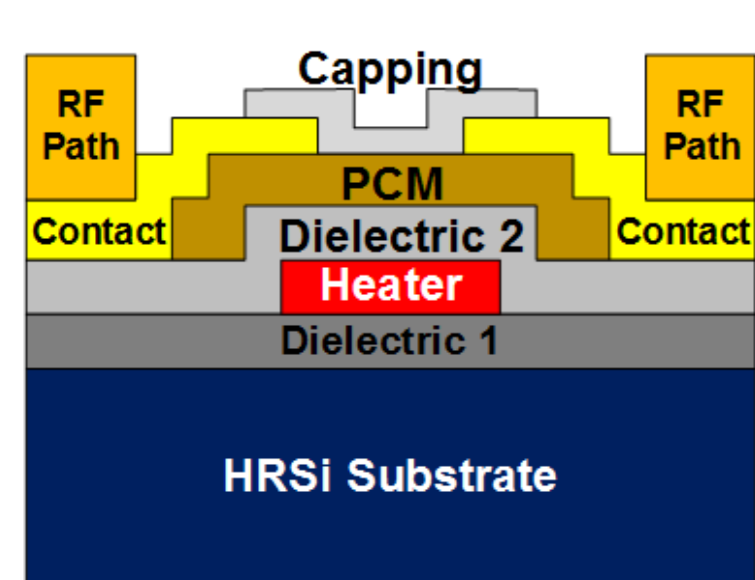
THE NEED FOR RECONFIGURABLE RF SYSTEMS

- Reduce the need for an RF chain for each band
- Add flexibility
- Reduce area and complexity
- Enable **block reutilization**
- Reduce **time-to-market** of radio transceivers
- Reduce **development costs**

OUR GOAL

- Develop fabrication process of indirectly-heated 4-terminal phase-change material (PCM)-based RF switch
- Design and fabricate **reconfigurable RF circuits** based on the PCM high performance RF switch

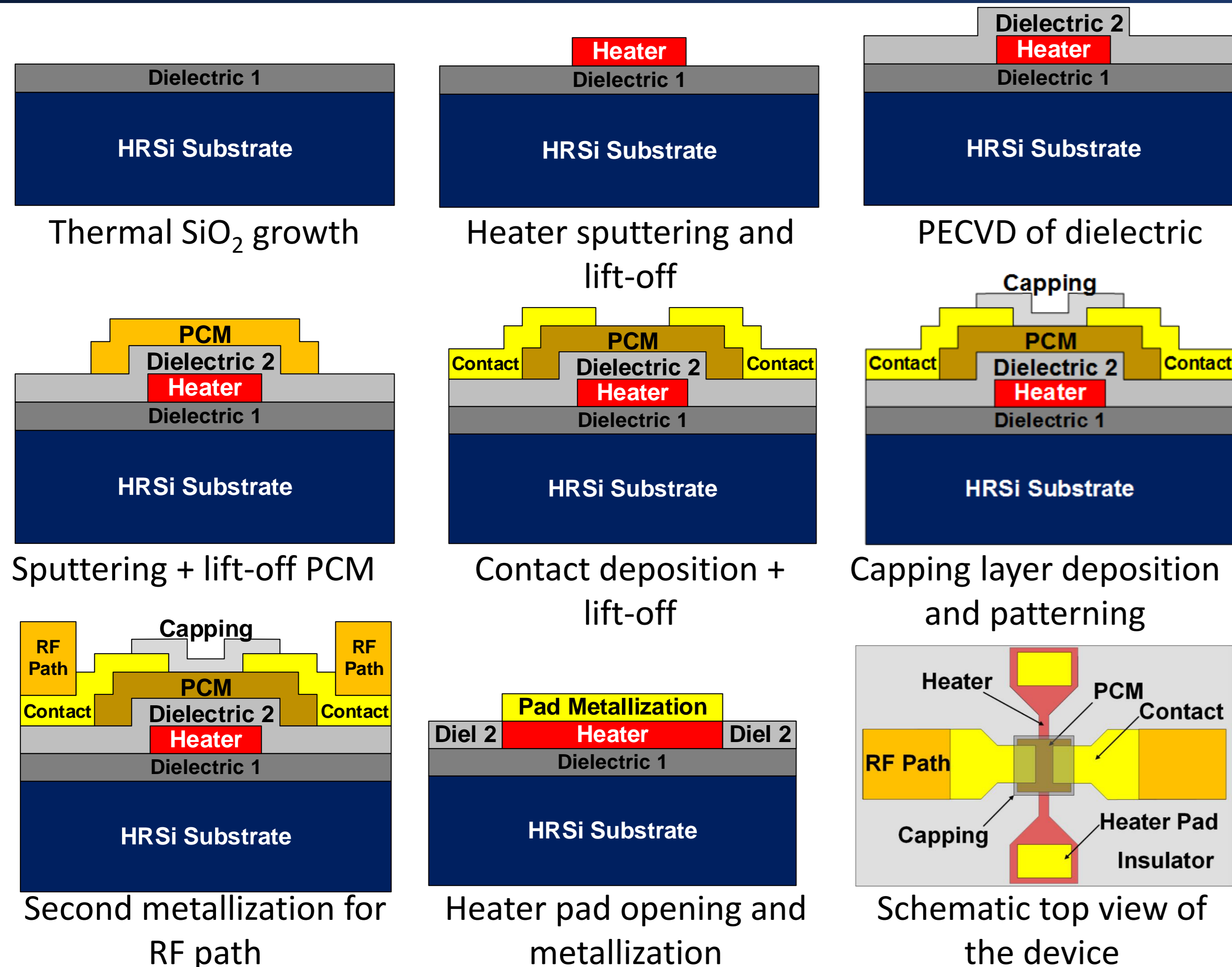
INDIRECTLY HEATED PCM RF SWITCH



- State-of-the-art FOM*
- Non-volatile
- Low-energy switching
- Fast-switching
- BEOL-compatible
- High linearity
- High endurance
- Low R_{ON}
- Small C_{OFF}

$$* FOM = (2\pi R_{ON} C_{OFF})^{-1}$$

FABRICATION PROCESS

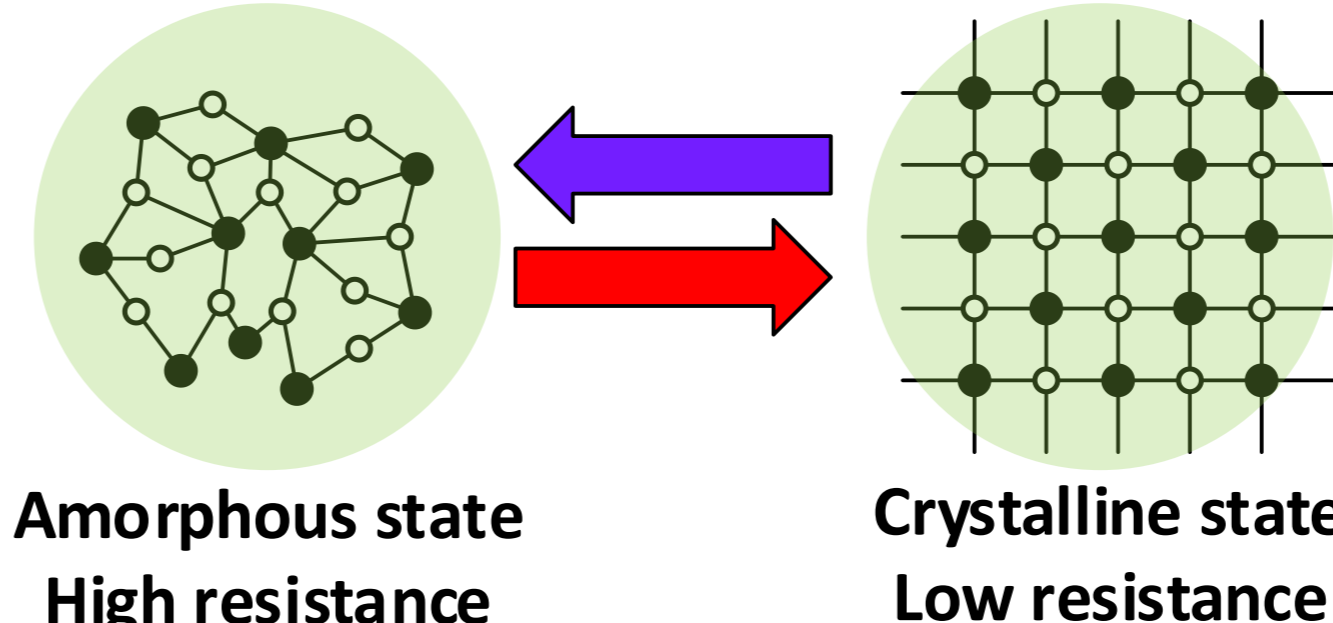


SUMMARY AND FUTURE WORK

- Developed process for high-performance PCM RF switch fabrication
- Electro-thermal modeling and characterization
- Design and fabrication of PCM-based reconfigurable circuits
- Exploration of the design space to optimize for different applications

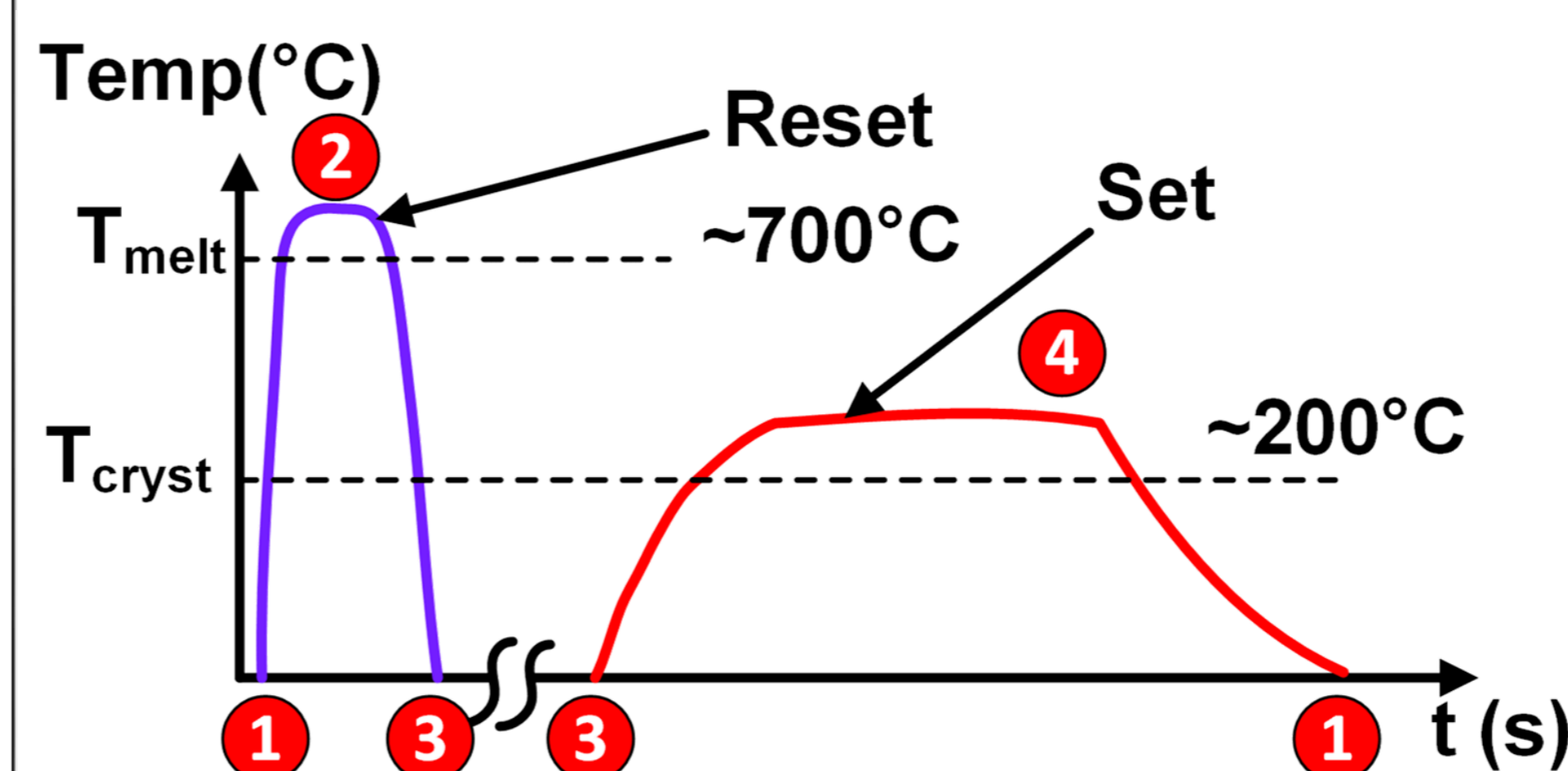
PHASE-CHANGE MATERIALS

THE OVSHINSKY PHENOMENA

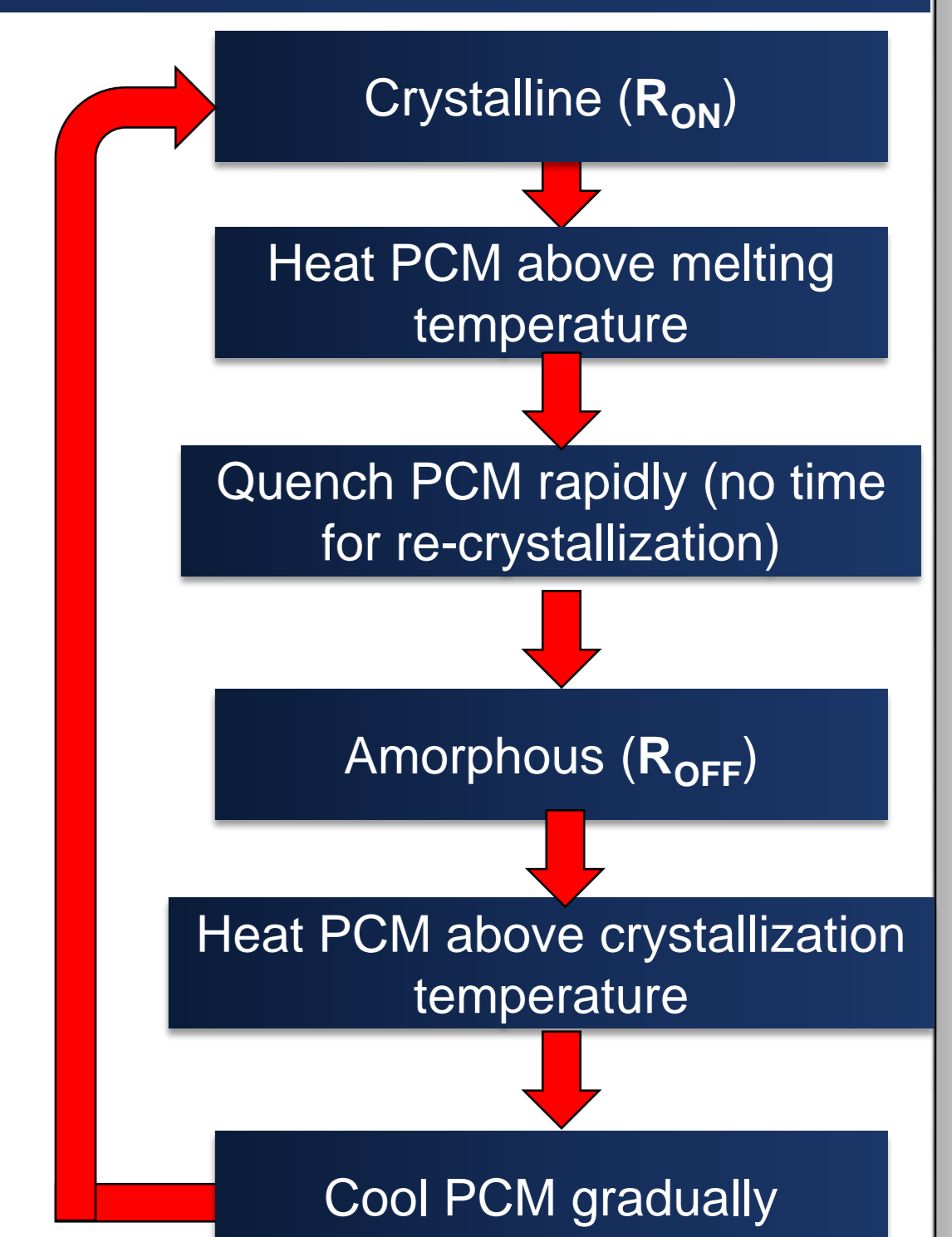


- Use of chalcogenide compounds
- Large R_{OFF}/R_{ON} contrast ($>10^3$)
- Commercial applications:
 - Non-volatile memories
 - Re-writable DVD's and CD's

PHASE TRANSFORMATION

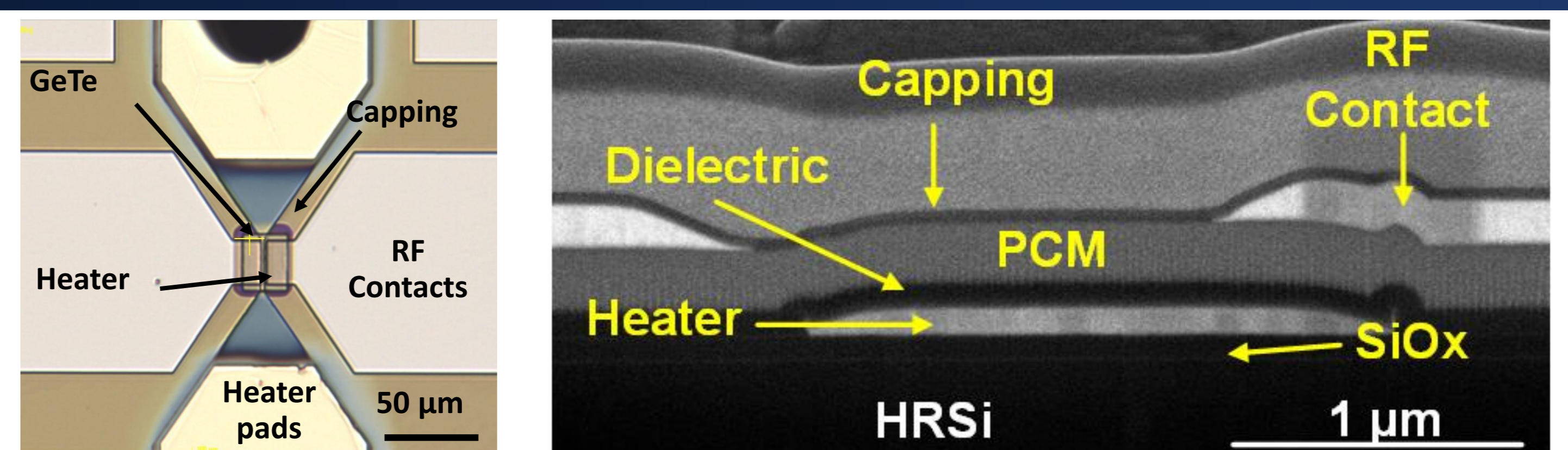


- $t_{set} \approx 1 \mu s$
- $t_{reset} \approx 100 ns$



RESULTS

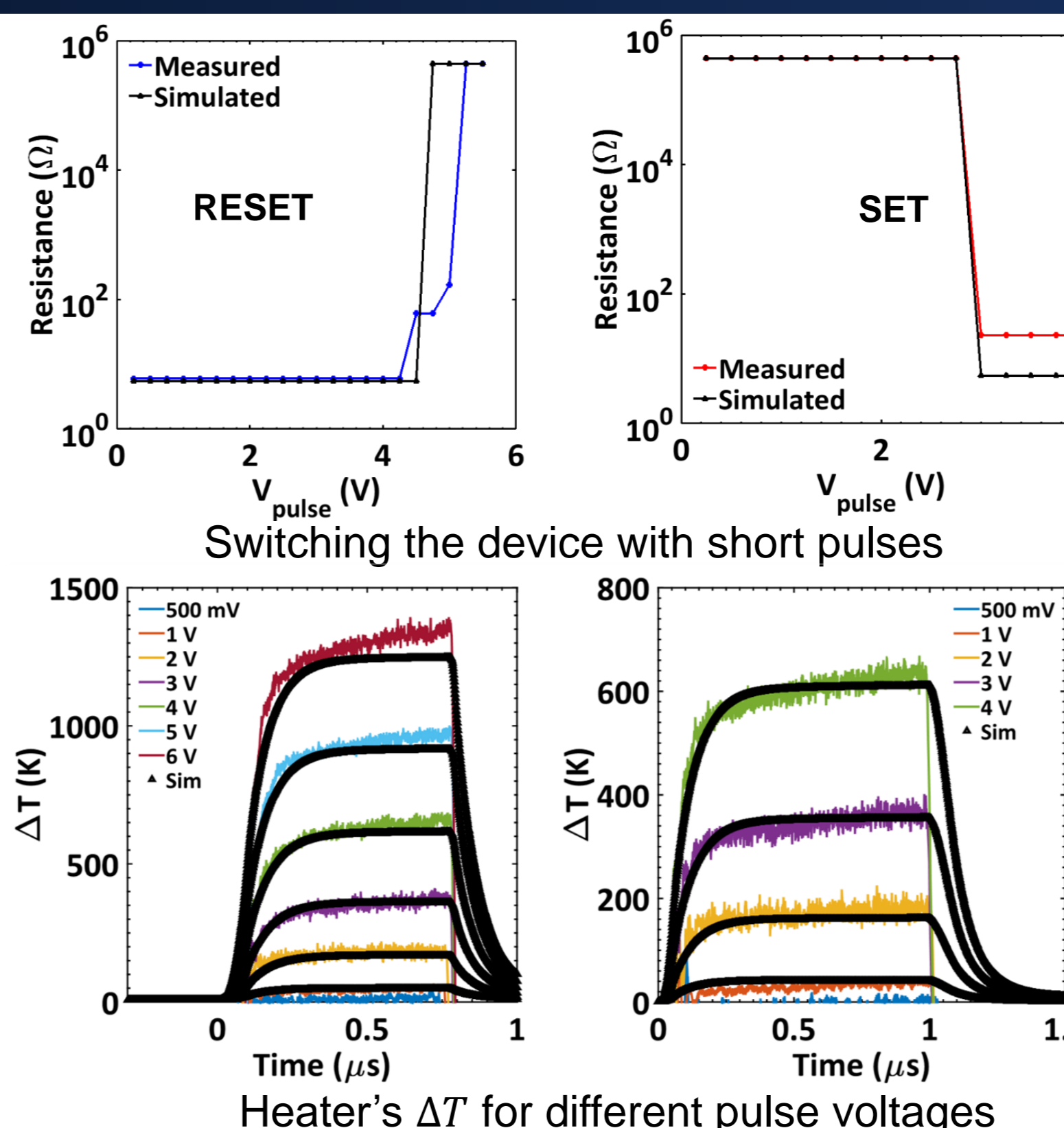
FABRICATION HIGHLIGHTS



Optical view of fabricated PCM RF switch

FIB cross-section of fabricated PCM RF switch

ELECTRO-THERMAL CHARACTERIZATION



- $R_{OFF}/R_{ON} > 10^4$
- $V_{SET} \approx 3.5 V$
- $V_{RESET} \approx 5 V$
- $R_{ON} = 2.3 \Omega$ for $W = 40 \mu m$ $L = 2 \mu m$

- $\Delta T_{RESET} = 915 K$
- $\Delta T_{SET} = 360 K$

REFERENCES

- [1] R. Singh *et al.*, IEEE MTT, 2017. [2] N. El-Hinnawy *et al.*, IEEE EDL, 2013. [3] N. El-Hinnawy *et al.*, IEEE CSICS, 2014. [4] J.S. Moon *et al.*, IEEE MTT, 2018. [5] M. Rais-Zadeh *et al.*, Proc. IEEE, 2015. [6] N. Wainstein *et al.*, IEEE TCAS I, 2018. [7] N. Wainstein *et al.*, IEEE TNANO, 2018. [8] N. Wainstein *et al.*, ISCAS 2017. [9] N. Wainstein *et al.*, ISVLSI 2019. [10] N. Wainstein *et al.*, Proc. IEEE (submitted). [11] N. Wainstein *et al.*, IEEE EDL (submitted).

ACKNOWLEDGMENTS

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